



FLASHATTENTION: 一种具有 IO 感知, 且兼具快速、内存高效的新型注意力算法

FLASHATTENTION: Fast and Memory-Efficient Exact Attention with IO-Awareness

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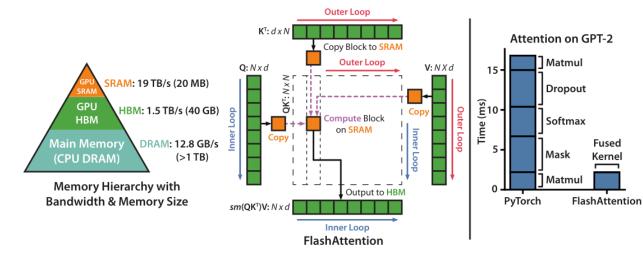
背景



Transformer 模型已是图像分类、自然语言处理等分支领域中最为常见的架构。这种模型核心的自注意力机制(self-attention)的时间和存储复杂度在序列长度上属于二次型。

于是有人提出近似注意力的方法,来减少注意力计算和内存需求。但它们过于关注降低每秒所执行的浮点运算次数(FLops),并且倾向于忽略来自内存访问(IO)的开销。







传统Attention



在传统的Attention中,Q,K,V作为输入,大小为N×d,如下图所示,在计算中需要存储中间值S和P到HBM中,这会极大占用HBM(高带宽显存)。

$$\mathbf{S} = \mathbf{Q}\mathbf{K}^{\top} \in \mathbb{R}^{N \times N}, \quad \mathbf{P} = \operatorname{softmax}(\mathbf{S}) \in \mathbb{R}^{N \times N}, \quad \mathbf{O} = \mathbf{P}\mathbf{V} \in \mathbb{R}^{N \times d},$$

Algorithm 0 Standard Attention Implementation

Require: Matrices $\mathbf{Q}, \mathbf{K}, \mathbf{V} \in \mathbb{R}^{N \times d}$ in HBM.

- 1: Load \mathbf{Q}, \mathbf{K} by blocks from HBM, compute $\mathbf{S} = \mathbf{Q}\mathbf{K}^{\mathsf{T}}$, write \mathbf{S} to HBM.
- 2: Read **S** from HBM, compute P = softmax(S), write **P** to HBM.
- 3: Load **P** and **V** by blocks from HBM, compute $\mathbf{O} = \mathbf{PV}$, write **O** to HBM.
- 4: Return O.





FLASH ATTENTION



FlashAttention旨在避免从 HBM(High Bandwidth Memory)中读取和写入注意力矩阵。这需要做到:

- (1)在不访问整个输入的情况下计算softmax函数的缩减;
- (2)在后向传播中不能存储中间注意力矩阵。

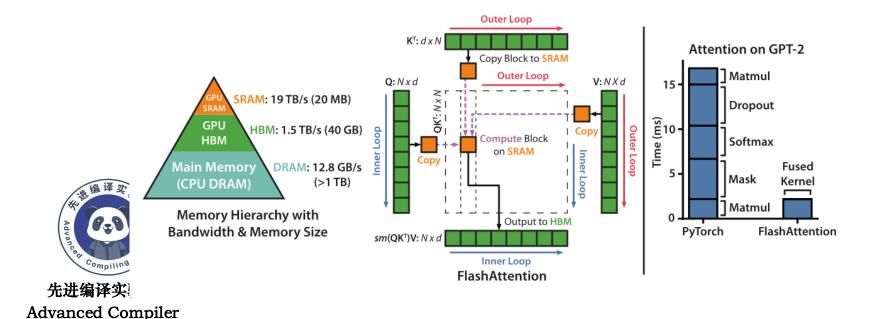




实现思路



标准Attention算法由于要计算softmax, 而softmax都是按行来计算的,按这个逻辑的话,在和V做矩阵乘之前,需要让 Q,K 的各个分块完成整一行分块的计算。得到Softmax的结果后,再和矩阵V分块做矩阵乘。而在Flash Attention中,将输入分割成块,并在输入块上进行多次传递,从而以增量方式执行softmax缩减。





实现思路



相比于标准Attention算法,Flash Attention并不需要存储中间注意力矩阵,存储前向传递的softmax归一化因子,以便在后向传递中快速重新计算芯片上的注意,这比从HBM读取中间注意矩阵的标准方法更快。

Algorithm 0 Standard Attention Implementation

Require: Matrices $\mathbf{Q}, \mathbf{K}, \mathbf{V} \in \mathbb{R}^{N \times d}$ in HBM.

- 1: Load \mathbf{Q}, \mathbf{K} by blocks from HBM, compute $\mathbf{S} = \mathbf{Q}\mathbf{K}^{\mathsf{T}}$, write \mathbf{S} to HBM.
- 2: Read S from HBM, compute P = softmax(S), write P to HBM.
- 3: Load **P** and **V** by blocks from HBM, compute $\mathbf{O} = \mathbf{PV}$, write \mathbf{O} to HBM.
- 4: Return **0**.



Advanced Compiler

Algorithm 2 FlashAttention Forward Pass Require: Matrices $\mathbf{Q}, \mathbf{K}, \mathbf{V} \in \mathbb{R}^{N \times d}$ in HBM, on

Require: Matrices $\mathbf{Q}, \mathbf{K}, \mathbf{V} \in \mathbb{R}^{N \times d}$ in HBM, on-chip SRAM of size M, softmax scaling constant $\tau \in \mathbb{R}$, masking function MASK, dropout probability p_{drop} .

- 1: Initialize the pseudo-random number generator state $\mathcal R$ and save to HBM.
- 2: Set block sizes $B_c = \left[\frac{M}{4d}\right], B_r = \min\left(\left[\frac{M}{4d}\right], d\right)$.
- 3: Initialize $\mathbf{O} = (0)_{N \times d} \in \mathbb{R}^{N \times d}, \ell = (0)_N \in \mathbb{R}^N, m = (-\infty)_N \in \mathbb{R}^N$ in HBM.
- 4: Divide **Q** into $T_r = \left\lceil \frac{N}{B_r} \right\rceil$ blocks $\mathbf{Q}_1, \dots, \mathbf{Q}_{T_r}$ of size $B_r \times d$ each, and divide \mathbf{K}, \mathbf{V} in to $T_c = \left\lceil \frac{N}{B_c} \right\rceil$ blocks $\mathbf{K}_1, \dots, \mathbf{K}_{T_c}$ and $\mathbf{V}_1, \dots, \mathbf{V}_{T_c}$, of size $B_c \times d$ each.
- 5: Divide $\mathbf{0}$ into T_r blocks $\mathbf{0}_i, \dots, \mathbf{0}_{T_r}$ of size $B_r \times d$ each, divide ℓ into T_r blocks $\ell_i, \dots, \ell_{T_r}$ of size B_r each, divide m into T_r blocks m_1, \dots, m_{T_r} of size B_r each.
- 6: for $1 \le j \le T_c$ do
- 7: Load \mathbf{K}_i , \mathbf{V}_i from HBM to on-chip SRAM.
- for $1 \le i \le T_r$ do
- Load $\mathbf{Q}_i, \mathbf{O}_i, \ell_i, m_i$ from HBM to on-chip SRAM.
- On chip, compute $\mathbf{S}_{ij} = \tau \mathbf{Q}_i \mathbf{K}_i^T \in \mathbb{R}^{B_r \times B_c}$.
- 11: On chip, compute $\mathbf{S}_{ij}^{\text{masked}} = \text{MASK}(\mathbf{S}_{ij})$.
- 12: On chip, compute $\tilde{m}_{ij} = \operatorname{rowmax}(\mathbf{S}_{ij}^{\operatorname{masked}}) \in \mathbb{R}^{B_r}$, $\tilde{\mathbf{P}}_{ij} = \exp(\mathbf{S}_{ij}^{\operatorname{masked}} \tilde{m}_{ij}) \in \mathbb{R}^{B_r \times B_c}$ (pointwise), $\tilde{\ell}_{ij} = \operatorname{rowsum}(\tilde{\mathbf{P}}_{ij}) \in \mathbb{R}^{B_r}$.
- $\text{On chip, compute } m_i^{\text{new}} = \max(m_i, \tilde{m}_{ij}) \in \mathbb{R}^{B_r}, \ \ell_i^{\text{new}} = e^{m_i m_i^{\text{new}}} \ell_i + e^{\tilde{m}_{ij} m_i^{\text{new}}} \tilde{\ell}_{ij} \in \mathbb{R}^{B_r}.$
- 14: On chip, compute $\tilde{\mathbf{P}}_{ij}^{\text{dropped}} = \text{dropout}(\tilde{\mathbf{P}}_{ij}, p_{\text{drop}})$.
- 15: Write $\mathbf{O}_i \leftarrow \mathrm{diag}(\ell_i^{\mathrm{new}})^{-1}(\mathrm{diag}(\ell_i)e^{m_i m_i^{\mathrm{new}}}\mathbf{O}_i + e^{\tilde{m}_{ij} m_i^{\mathrm{new}}}\tilde{\mathbf{P}}_{ij}^{\mathrm{dropped}}\mathbf{V}_j)$ to HBM.
- 16: Write $\ell_i \leftarrow \ell_i^{\text{new}}$, $m_i \leftarrow m_i^{\text{new}}$ to HBM.
- 17: end for
- 18: end for
- 19: Return $\mathbf{O}, \ell, m, \mathcal{R}$.

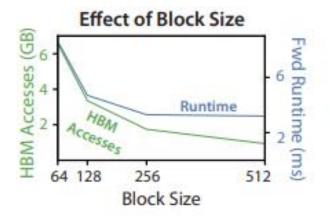


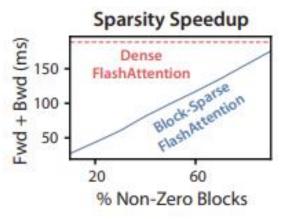
结果



对比标准的Attention机制,Flash Attention虽然由于向后传播需要重新计算导致GFLOPs增加,但是Flash Attention对HBM的I/O和运行时间都有了显著的提高,如下图所示,我们可以看出Flash Attention在I/O减少和加速都有不错的效果。(A100GPU、GPT-2模型)。

Attention	Standard	FLASHATTENTION
GFLOPs	66.6	75.2
HBM R/W (GB)	40.3	4.4
Runtime (ms)	41.7	7.3





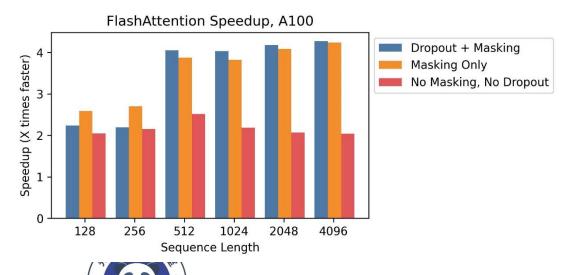


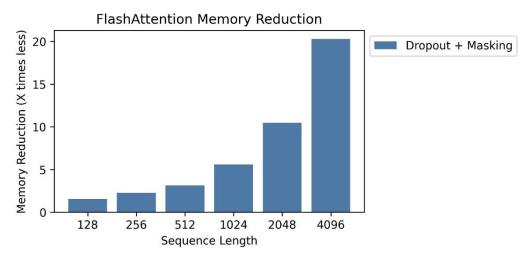


结果



如图所示,Flash-Attention算法在A100显卡上的加速效果,在不同的序列长度下都有不同程度的加速效果。而在右图中展示了随着序列长度的增加,Flash-Attention对于内存消耗有着不断提升的效果。











Flash Attention的主要目的是加速和节省内存。主要贡献点:

- 1.计算softmax时候不需要全量input数据,可以分段计算。
- 2.反向传播的时候,不存储attention matrix (N^2的矩阵),而是只存

储softmax归一化的系数。Algorithm 1 FLASHATTENTION

Require: Matrices $\mathbf{Q}, \mathbf{K}, \mathbf{V} \in \mathbb{R}^{N \times d}$ in HBM, on-chip SRAM of size M.

- 1: Set block sizes $B_c = \left\lceil \frac{M}{4d} \right\rceil$, $B_r = \min\left(\left\lceil \frac{M}{4d} \right\rceil, d \right)$.
- 2: Initialize $\mathbf{0} = (0)_{N \times d} \in \mathbb{R}^{N \times d}, \ell = (0)_{N} \in \mathbb{R}^{N}, m = (-\infty)_{N} \in \mathbb{R}^{N}$ in HBM.
- 3: Divide **Q** into $T_r = \begin{bmatrix} \frac{N}{B_r} \end{bmatrix}$ blocks $\mathbf{Q}_1, \dots, \mathbf{Q}_{T_r}$ of size $B_r \times d$ each, and divide \mathbf{K}, \mathbf{V} in to $T_c = \begin{bmatrix} \frac{N}{B_c} \end{bmatrix}$ blocks $\mathbf{K}_1, \dots, \mathbf{K}_{T_c}$ and $\mathbf{V}_1, \dots, \mathbf{V}_{T_c}$, of size $B_c \times d$ each.
- 4: Divide **0** into T_r blocks $\mathbf{0}_i, \dots, \mathbf{0}_{T_r}$ of size $B_r \times d$ each, divide ℓ into T_r blocks $\ell_i, \dots, \ell_{T_r}$ of size B_r each divide m into T_r blocks m_1, \ldots, m_{T_r} of size B_r each.
- 5: for $1 \le j \le T_c$ do
- Load \mathbf{K}_i , \mathbf{V}_i from HBM to on-chip SRAM.
- for $1 \le i \le T_r$ do
- Load $\mathbf{Q}_i, \mathbf{O}_i, \ell_i, m_i$ from HBM to on-chip SRAM.
- On chip, compute $\mathbf{S}_{ij} = \mathbf{Q}_i \mathbf{K}_i^T \in \mathbb{R}^{B_r \times B_c}$.
- On chip, compute $\tilde{m}_{ij} = \text{rowmax}(\mathbf{S}_{ij}) \in \mathbb{R}^{B_r}$, $\tilde{\mathbf{P}}_{ij} = \exp(\mathbf{S}_{ij} \tilde{m}_{ij}) \in \mathbb{R}^{B_r \times B_c}$ (pointwise), $\tilde{\ell}_{ij} = \exp(\mathbf{S}_{ij} \tilde{m}_{ij})$ $\operatorname{rowsum}(\tilde{\mathbf{P}}_{ij}) \in \mathbb{R}^{B_r}$.
- On chip, compute $m_i^{\text{new}} = \max(m_i, \tilde{m}_{ij}) \in \mathbb{R}^{B_r}$, $\ell_i^{\text{new}} = e^{m_i m_i^{\text{new}}} \ell_i + e^{\tilde{m}_{ij} m_i^{\text{new}}} \tilde{\ell}_{ij} \in \mathbb{R}^{B_r}$.
- Write $\mathbf{O}_i \leftarrow \operatorname{diag}(\ell_i^{\text{new}})^{-1}(\operatorname{diag}(\ell_i)e^{m_i-m_i^{\text{new}}}\mathbf{O}_i + e^{\tilde{m}_{ij}-m_i^{\text{new}}}\tilde{\mathbf{P}}_{ij}\mathbf{V}_i)$ to HBM. 12:
- Write $\ell_i \leftarrow \ell_i^{\text{new}}$, $m_i \leftarrow m_i^{\text{new}}$ to HBM.
- end for
- 15: end for
- 16: Return **O**.





参考资料



FlashAttention: Fast and Memory-Efficient Exact Attention with IO-Awareness

https://gitcode.net/mirrors/HazyResearch/flash-attention?utm_source=csdn_github_accelerator

https://zhuanlan.zhihu.com/p/567167376



